
HVC133

Silicon Epitaxial Planar Pin Diode for High Frequency Switching

HITACHI

ADE-208-423A(Z)

Rev 1

September 1996

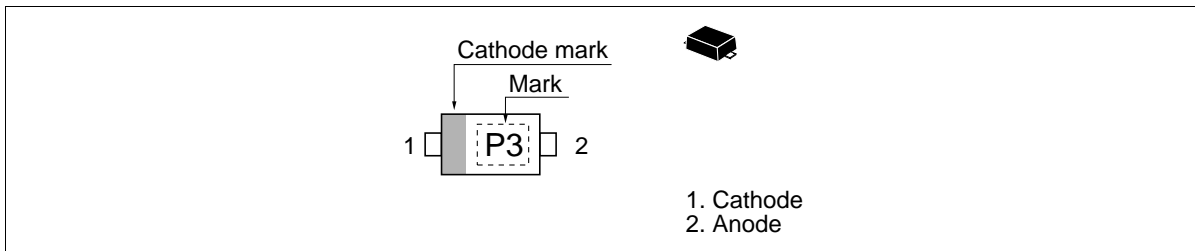
Features

- Low capacitance. ($C1=1.0\text{pF}$ max)
- Low forward resistance. ($r_f=0.7\Omega$ max)
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVC133	P3	UFP

Outline



HVC133

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	30	V
Power dissipation	Pd	150	mW
Junction temperature	TJ	125	°C
Storage temperature	Tstg	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	30	∞	∞	V	IR = 1μA
Reverse current	IR	∞	∞	100	nA	VR = 25V
Forward voltage	VF	∞	∞	0.85	V	IF = 2 mA
Capacitance	C1	∞	∞	1.0	pF	VR = 1V, f = 1 MHz
	C6	∞	∞	0.9		VR = 6V, f = 1 MHz
Forward resistance	rf	∞	0.55	0.7	Ω	IF = 2mA, f = 100 MHz

Main Characteristic

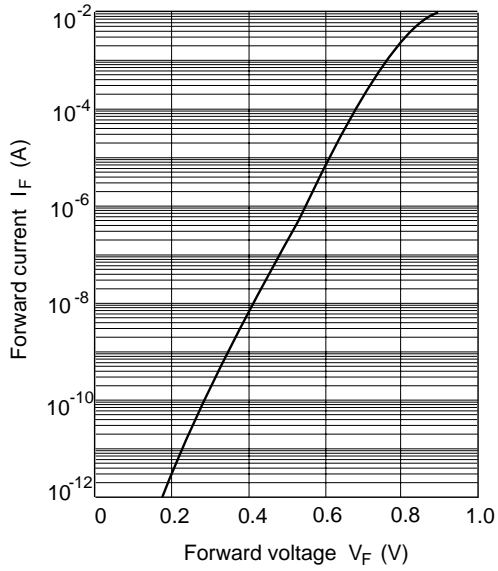


Fig.1 Forward current Vs. Forward voltage

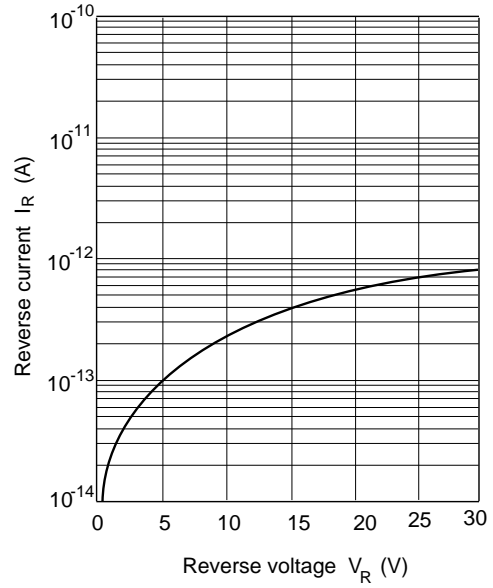


Fig.2 Reverse current Vs. Reverse voltage

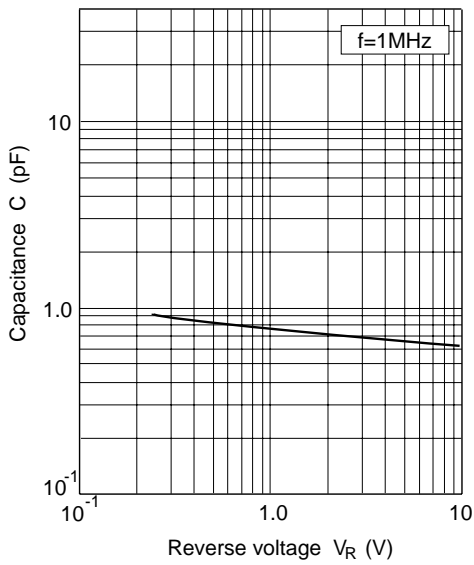


Fig.3 Capacitance Vs. Reverse voltage

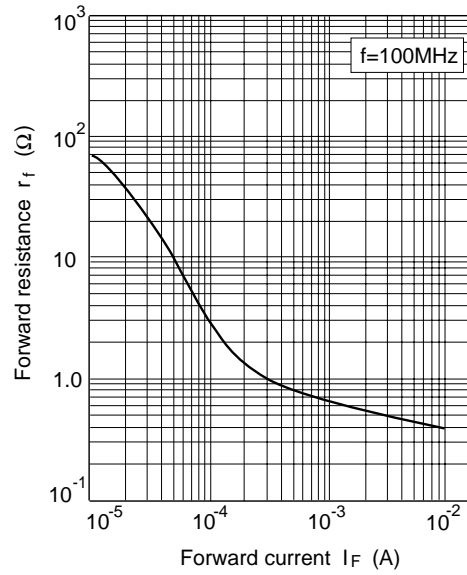


Fig.4 Forward resistance Vs. Forward current

HVC133

Package Dimensions

Unit : mm

